

MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

M54517P

7-UNIT 400mA DARLINGTON TRANSISTOR ARRAY

DESCRIPTION

M54517P is seven-circuit Darlington transistor arrays. The circuits are made of NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

FEATURES

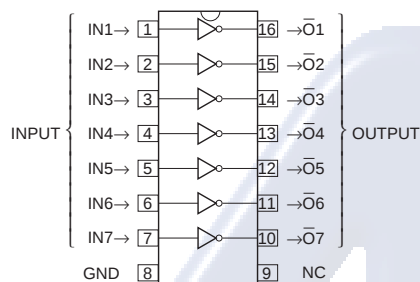
- Medium breakdown voltage ($BV_{CEO} \geq 25V$)
- High-current driving ($I_{c(max)} = 400mA$)
- Driving available with PMOS IC output
- Wide operating temperature range ($T_a = -20$ to $+75^\circ C$)

APPLICATION

Drives of relays and printers, digit drives of indication elements (LEDs and lamps), and MOS-bipolar logic IC interfaces

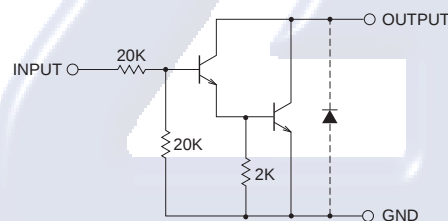
FUNCTION

The M54517P has seven circuits consisting of NPN Darlington transistors. These ICs have resistance of $20k\Omega$ between input transistor bases and input pins. The output transistor emitters are all connected to the GND pin (pin 8). Collector current is 400mA maximum. Collector-emitter supply voltage is 25V maximum.

PIN CONFIGURATION

Package type 16P4

NC : No connection

CIRCUIT DIAGRAM

The seven circuits share the GND.

The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit : Ω **ABSOLUTE MAXIMUM RATINGS** (Unless otherwise noted, $T_a = -20 \sim +75^\circ C$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CEO}	Collector-emitter voltage	Output, H	$-0.5 \sim +25$	V
I_c	Collector current	Current per circuit output, L	400	mA
V_i	Input voltage		$-0.5 \sim +25$	V
P_d	Power dissipation	$T_a = 25^\circ C$, when mounted on board	1.47	W
T_{opr}	Operating temperature		$-20 \sim +75$	$^\circ C$
T_{stg}	Storage temperature		$-55 \sim +125$	$^\circ C$

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RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, Ta = -20 ~ +75°C)

Symbol	Parameter		Limits			Unit
			min	typ	max	
Vo	Output voltage		0	—	25	V
Ic	Collector current (Current per 1 circuit when 7 circuits are coming on simultaneously)	Duty Cycle no more than 8%	0	—	400	mA
		Duty Cycle no more than 40%	0	—	200	
VIH	"H" input voltage	Ic ≤ 400mA	8	—	20	V
		Ic ≤ 200mA	5	—		
ViL	"L" input voltage		0	—	0.5	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, Ta = -20 ~ +75°C)

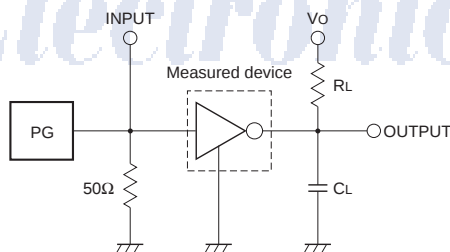
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ*	max	
V (BR) CEO	Collector-emitter breakdown voltage	ICEO = 100μA	25	—	—	V
VCE (sat)	Collector-emitter saturation voltage	VI = 8V, IC = 400mA	—	1.15	2.2	V
		VI = 5V, IC = 200mA	—	0.95	1.4	
II	Input current	VI = 17V	0.3	0.8	1.8	mA
hFE	DC amplification factor	VCE = 4V, IC = 400mA, Ta = 25°C	1000	4500	—	—

* : The typical values are those measured under ambient temperature (Ta) of 25°C. There is no guarantee that these values are obtained under any conditions.

SWITCHING CHARACTERISTICS (Unless otherwise noted, Ta = 25°C)

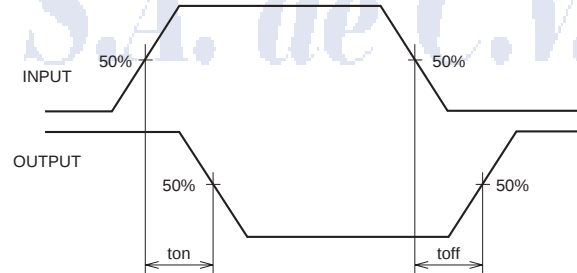
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
ton	Turn-on time	CL = 15pF (note 1)	—	50	—	ns
toff	Turn-off time		—	500	—	ns

NOTE 1 TEST CIRCUIT



- (1) Pulse generator (PG) characteristics : PRR = 1kHz, tw = 10μs, tr = 6ns, tf = 6ns, Zo = 50Ω, Vp = 8Vp-p
- (2) Input-output conditions : RL = 25Ω, Vo = 10V
- (3) Electrostatic capacity CL includes floating capacitance at connections and input capacitance at probes

TIMING DIAGRAM

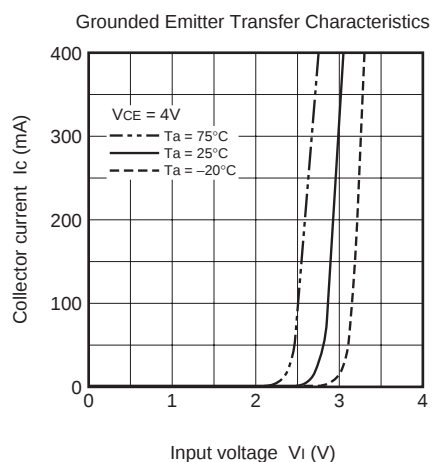
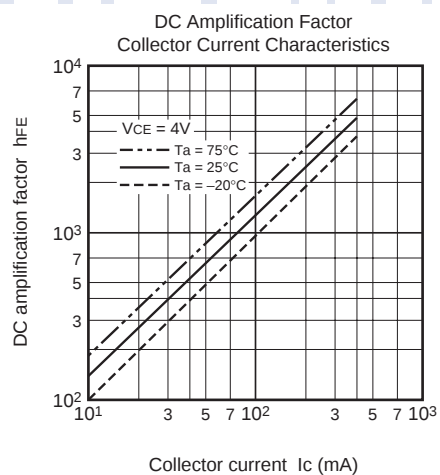
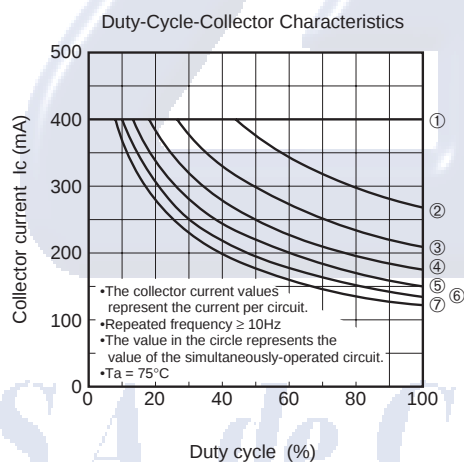
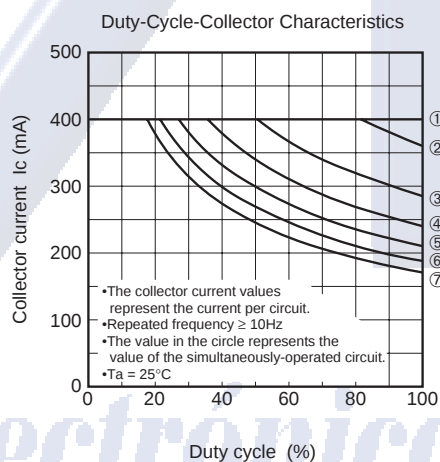
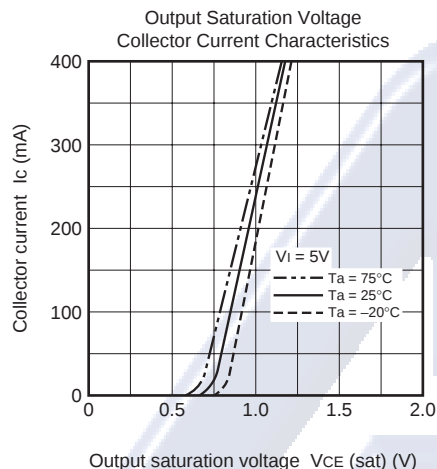
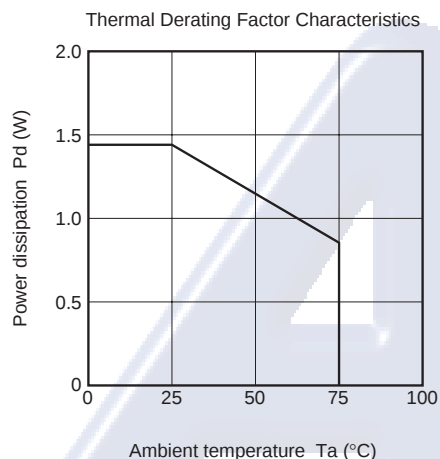


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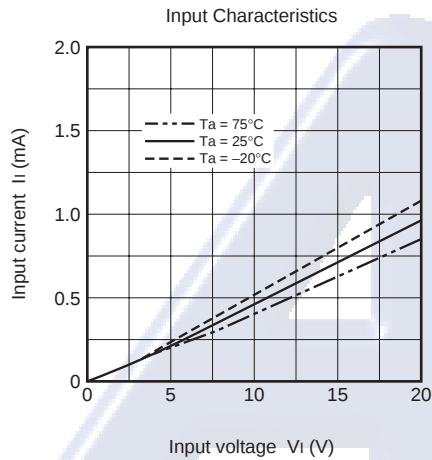
TYPICAL CHARACTERISTICS



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Electrónica S.A. de C.V.

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